

# OPA6610

High Bright

## Red LED Chip

GaAlAs / GaAs

**1. Material** Substrate GaAs (P Type)  
Epitaxial Layer GaAlAs (N/P Type)

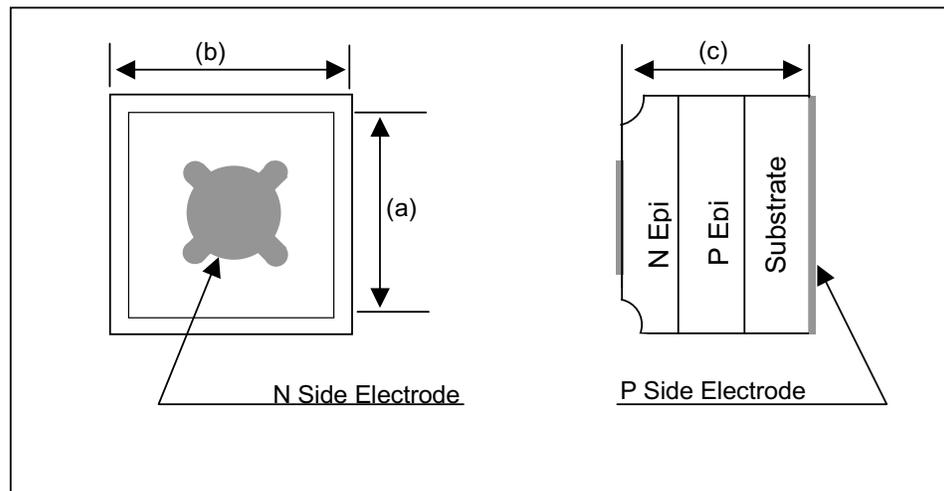
**2. Electrode** N (Cathode) Side Gold Alloy  
P (Anode) Side Gold Alloy

### 3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	$I_F=1mA$
	$V_{F(2)}$		1.8	2.1	V	$I_F=20mA$
Reverse Voltage	$V_R$	5.0			V	$I_R=10\mu A$
Brightness	$I_V$	200	350		mcd	$I_F=20mA$
Wavelength	Hue		645		nm	$I_F=20mA$
	$\Delta\lambda$		20		nm	$I_F=20mA$

※ Note: Assembled into T1<sup>3</sup>/<sub>4</sub> plastic package.

**4. Mechanical Data** (a) Emission Area ----- 9mil × 9mil  
(b) Bottom Area ----- 11mil × 11mil  
(c) Chip Thickness ----- 11mil



Knowledge\*on Inc.

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